

3.3 V Dual LVTTL/LVCMOS to Differential LVPECL Translator

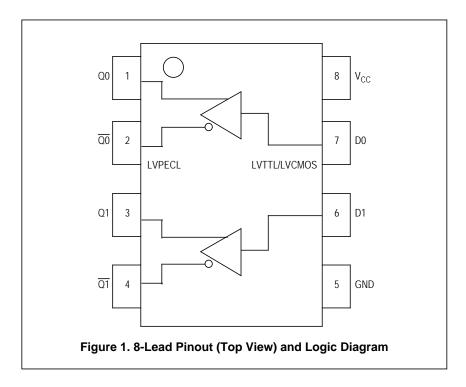
Product Discontinuance Notice – Last Time Buy Expires on (12/12/2013)

DATASHEET

The MC100ES60T22 is a low skew dual LVTTL/LVCMOS to differential LVPECL translator. The low voltage PECL levels, small package, and dual gate design are ideal for clock translation applications.

Features

- 280 ps typical propagation delay
- 100 ps max output-to-output skew
- LVPECL operating range: $V_{CC} = 3.135 \text{ V}$ to 3.8 V
- 8-lead SOIC and 8-lead TSSOP packages
- Ambient temperature range -40°C to +85°C
- 8-lead SOIC Pb-free package available
- Use Replacement Part: ICS85322I



1

MC100ES60T22



8-LEAD SOIC PACKAGE CASE 751-07



FF SUFFIX 8-LEAD SOIC PACKAGE Pb-FREE PACKAGE CASE 751-07



8-LEAD TSSOP PACKAGE CASE 1640-01

ORDERING INFORMATION								
Device	Package							
MC100ES60T22D	SOIC-8							
MC100ES60T22DR2	SOIC-8							
MC100ES60T22EF	SOIC-8 (Pb-Free)							
MC100ES60T22EFR2	SOIC-8 (Pb-Free)							
MC100ES60T22DT	TSSOP-8							
MC100ES60T22DTR2	TSSOP-8							

PIN DESCRIPTION								
Pin Function								
D0, D1	LVTTL/LVCMOS Inputs							
Qn, Qn	LVPECL Differential Outputs							
V _{CC}	Positive Supply							
GND	Negative Supply							

Table 1. General Specifications

Charac	Value	
Internal Input Pulldown Resistor	75 kΩ	
Internal Input Pullup Resistor	75 kΩ	
ESD Protection	Human Body Model Machine Model	> 2000 V > 200 V
θ _{JA} Thermal Resistance (Junction-to-Ambient)	0 LFPM, 8 SOIC 500 LFPM, 8 SOIC 0 LFPM, 8 TSSOP 500 LFPM, 8 TSSOP	190°C/W 130°C/W 185°C/W 140°C/W

Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test

Table 2. Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Conditions	Rating	Units
V _{SUPPLY}	Power Supply Voltage	Difference between V _{CC} & V _{EE}	3.9	V
V _{IN}	Input Voltage	$V_{CC} - V_{EE} \le 3.6 \text{ V}$	V _{CC} + 0.3 V _{EE} - 0.3	V V
l _{out}	Output Current	Continuous Surge	50 100	mA mA
T _A	Operating Temperature Range		-40 to +85	°C
T _{STG}	Storage Temperature Range		-65 to +150	°C

^{1.} Absolute maximum continuous ratings are those maximum values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation at absolute-maximum-rated conditions is not implied.

Table 3. DC Characteristics ($V_{CC} = 3.135 \text{ V to } 3.8 \text{ V}; V_{EE} = 0 \text{ V}$)

			-40°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Unit
V _{OH} ⁽¹⁾	Output HIGH Voltage	V _{CC} – 1150	V _{CC} – 1020	V _{CC} – 800	V _{CC} – 1200	V _{CC} – 970	V _{CC} – 750	mV
V _{OL} ⁽¹⁾	Output LOW Voltage	V _{CC} – 1950	V _{CC} – 1620	V _{CC} – 1250	V _{CC} – 2000	V _{CC} – 1680	V _{CC} – 1300	mV

^{1.} Outputs are terminated through a 50 Ω resistor to V_{CC} – 2 volts.

Table 4. LVTTL / LVCMOS Input DC Characteristics ($V_{CC} = 3.135 \text{ V to } 3.8 \text{ V}$)

			-40°C		0°C to 85°C				
Symbol	Characteristic	Condition	Min	Тур	Max	Min	Тур	Max	Unit
I _{IN}	Input Current	$V_{IN} = V_{CC}$			±150			±150	μА
V _{IK}	Input Clamp Voltage	$I_{IN} = -18 \text{ mA}$			-1.2			-1.2	V
V _{IH}	Input HIGH Voltage		2.0		V _{CC} +0.3	2.0		V _{CC} +0.3	V
V _{IL}	Input LOW Voltage				0.8			0.8	V

Table 5. AC Characteristics (V_{CC} = 3.134 V to 3.8 V; V_{EE} = 0 V)

		-40°C			25°C			85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Toggle Frequency			1			1			1	GHz
t _{PLH,} t _{PHL}	Propagation Delay	100	260	400	100	280	400	100	280	450	ps
t _{SKEW}	Skew part-to-part			300			300			350	ps
t _{JITTER}	Cycle-to-Cycle Jitter RMS (1σ)			1			1			1	ps
V _{outPP}	Output Peak-to-Peak Voltage	350	750		350	750		350	750		mV
t _r / t _f	Output Rise/Fall Times (20% – 80%)	50		400	50		400	50		400	ps

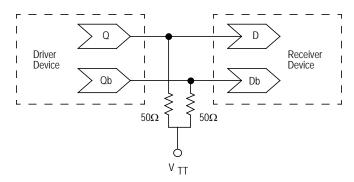
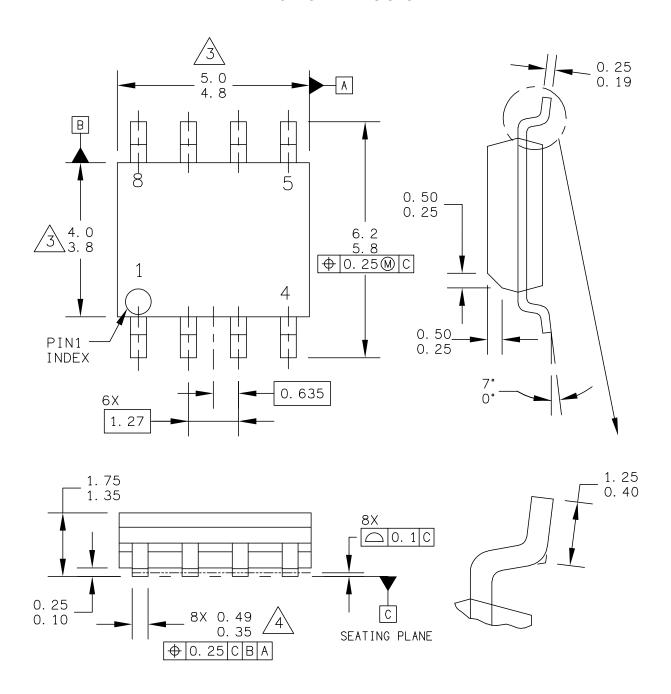


Figure 2. Typical Termination for Output Driver and Device Evaluation

PACKAGE DIMENSIONS



	MECHANICAL OUTLINE			PRINT VERSION NO	OT TO SCALE		
TITLE:					DOCUMENT NO): 98ASB42564B	REV: U
	8LD	SOIC	NARROW	BODY	CASE NUMBER	2: 751–07	07 APR 2005
					STANDARD: JE	IDEC MS-012AA	

PAGE 1 OF 2

CASE 751-07 ISSUE U 8-LEAD SOIC PACKAGE

PACKAGE DIMENSIONS

NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

0.15 PER SIDE.

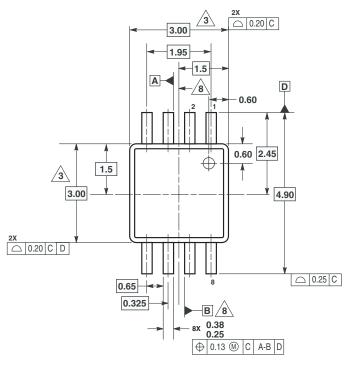
DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MECHANICAL OUTLINE				PRINT VERSION NO	OT TO SCALE	
TITLE:					DOCUMENT NO): 98ASB42564B	REV: U
	8LD	SOIC	NARROW	BODY	CASE NUMBER	2: 751–07	07 APR 2005
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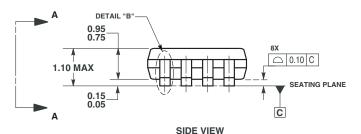
PAGE 2 OF 2

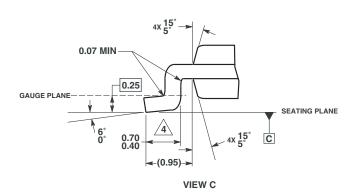
CASE 751-07 ISSUE U 8-LEAD SOIC PACKAGE

PACKAGE DIMENSIONS

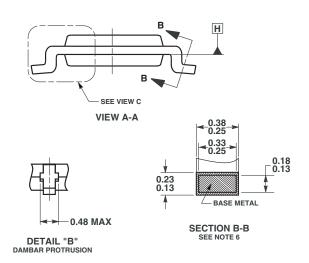








CASE 1640-01 ISSUE O 8-LEAD TSSOP PACKAGE



NOTES:

- I. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. DIMENSIONS ARE IN MILLIMETERS.
- 3. THIS DIMENSION DOES NOT INCLUDE MOLD FLASH OR PROTRUSIONS
 AND ARE MEASURED AT DATUM H, MOLD FLASH OR PROTRUSIONS,
 SHALL NOT EXCEED 0.15mm PER SIDE.
- 4 DIMENSION IS THE LENGTH OF TERMINAL FOR SOLDERING TO A SUBSTRATE.
- SUBSTINATE.

 THE LEAD WIDTH DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION.
 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08mm TOTAL IN EXCESS
 OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE LEAD
 FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD
 TO BE 0.14mm SEE DETAIL "B" AND SECTION B-B.
- 6. SECTION B-B TO BE DETERMINED AT 0.10 TO 0.25mm FROM THE LEAD TIP.
 7. THIS PART IS COMPLIANT WITH JEDEC REGISTRATION MO-187 AA.
 8. DATUMS A AND B TO BE DETERMINED DATUM PLANE H.

Revision History Sheet

Rev	Table	Page	Description of Change	Date
3		1	Product Discontinuance Notice – Last Time Buy Expires on (12/12/2013)	1/9/13
4		1	PDN# N-12-32R1, Added replacement part number	10/2/13

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